LGE3M70120J

Silicon Carbide Power MOSFET

V_{DS} = 1200 V
I_D@25ºC = 36A
$R_{DS(ON)}$ = 68mΩ
AEC-Q101 and PPAP capable

Features

- High Blocking Voltage
- High Frequency Operation
- Low on-resistance
- Fast intrinsic diode with low reverse recovery
- 100% avalanche tested

Benefits

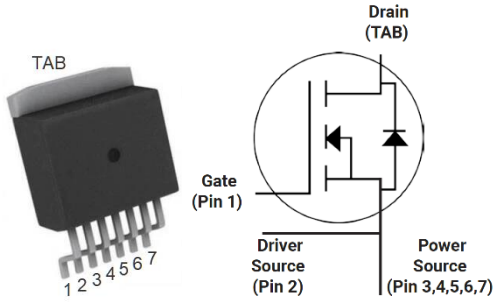
- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- High Temperature Application
- Hard Switching & Higher Reliability
- Easy to drive

Applications

- Motor Drives
- Solar / Wind Inverters
- EV Charging Station

- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

TO-263-7



Part Number	Package	Marking
LGE3M70120J	TO-263-7	LGE3M70120J

Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DSmax}	Drain - Source Voltage		1200	V
V_{GSmax}	Gate - Source Voltage (dynamic), T_{surge} <100ns		-10 / +25	V
V_{GSop}	Gate - Source Voltage (static)		-5 / +20	V
I_D	Continuous Drain Current	V_{GS} = 20V, T_C=25°C V_{GS} = 20V, T_C=100°C	36 25	A
$I_{D(pulse)}$	Pulsed Drain Current at T_C=25°C		85	A
E_{AS}	Avalanche Energy	V_{DD} = 100V, V_{GS}=20V, L=2mH	256	mJ
I_{AV}	Avalanche Peak Current		16	A
P_D	Total power dissipation	T_C=25°C	192	W
T_J	Operating Junction Temperature		-40 to 175	°C
T_{STG}	Storage Temperature		-40 to 175	°C

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Electrical Characteristics (T_C=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 100μA	1200			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 5mA	1.8	2.6	3.6	V
		V_{DS} = V_{GS}, I_D = 5mA, T_J = 150°C		1.9		
		V_{DS} = V_{GS}, I_D = 5mA, T_J = 175°C		1.8		
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1200V, V_{GS} = 0V	0	1	50	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS} = 20V, V_{DS} = 0V	0	1	200	nA
Gate-Source Leakage Current	I_{GSS}	V_{GS} = -5V, V_{DS} = 0V	-200	-1	0	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 20V, I_D = 20 A		68	85	mΩ
		V_{GS} = 20V, I_D = 20 A, T_J = 150°C		108		
		V_{GS} = 20V, I_D = 20 A, T_J = 175°C		122		
Transconductance	g_{fs}	V_{DS} = 20V, I_D = 20 A,		10.3		S
		V_{DS} = 20V, I_D = 20 A, T_J = 150°C		9.7		
		V_{DS} = 20V, I_D = 20 A, T_J = 175°C		9.6		
Input capacitance	C_{iss}	V_{DS} = 1000V, V_{GS} = 0V f = 1MHz		1340		pF
Output capacitance	C_{oss}			63		
Reverse transfer capacitance	C_{rss}			4		
C_{oss} Stored Energy	E_{oss}			41		μJ
Total gate charge	Q_g	V_{DS} = 800V, V_{GS} = -5V / 20V I_D = 20 A,		69		nC
Gate-source charge	Q_{gs}			20		
Gate-drain charge	Q_{gd}			24		
Internal gate input resistance	$R_{g(int)}$	f = 1MHz, I_D = 0A		2.5		Ω
Series Inductance	L_S	f = 1MHz		4.5		nH
Turn-On Switching Energy	E_{ON}	V_{DS} = 800 V, V_{GS} = -5V/20V, I_D = 20A, $R_{G(ext)}$ =2Ω, L=100μH		210		μJ
Turn-Off Switching Energy	E_{OFF}			25		
Turn-On Delay Time	$t_{d(on)}$			10		ns
Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(off)}$			21		
Fall Time	t_f			9		

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Reverse Diode Characteristics (T_C=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Diode Forward Voltage	V_{SD}	V_{GS} = -5V, I_{SD} = 10A,		4.4		V
		V_{GS} = -5V, I_{SD} = 10A, T_J = 150°C		4.0		
		V_{GS} = -5V, I_{SD} = 10A, T_J = 175°C		3.9		
Continuous Diode Forward Current	I_S	V_{GS} = -5V			31	A
Reverse Recovery time	t_{rr}	V_{GS} = -5V, I_{SD} = 20A, V_R= 800V, dif/dt = 3100 A/μs		22		ns
Reverse Recovery Charge	Q_{rr}			160		nC
Peak Reverse Recovery Current	I_{rrm}			17		A

Thermal Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$R_{th(j-c)}$	Thermal resistance from junction to case		0.64	0.78	^{0}C/W

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Typical Performance

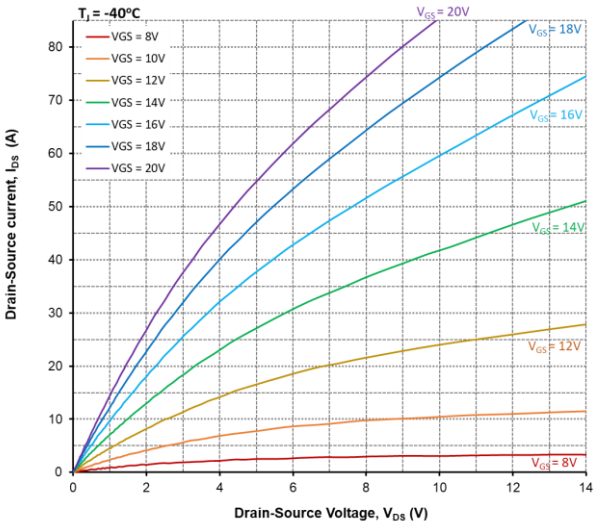


Figure 1. Output Characteristics, T_J = -40°C

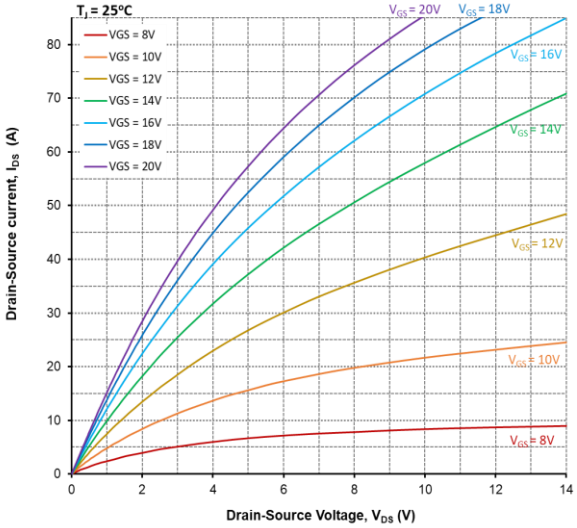


Figure 2. Output Characteristics, T_J = 25°C

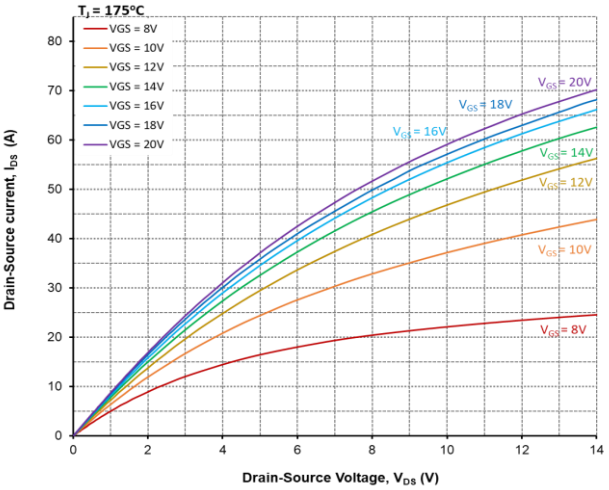


Figure 3. Output Characteristics, T_J = 175°C

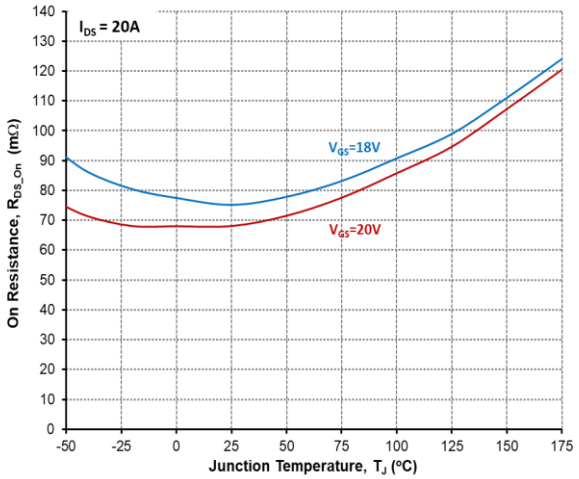


Figure 4. On-Resistance vs. Temperature

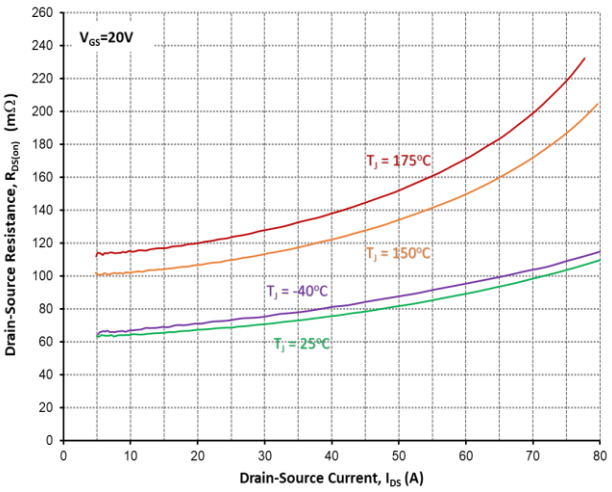


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

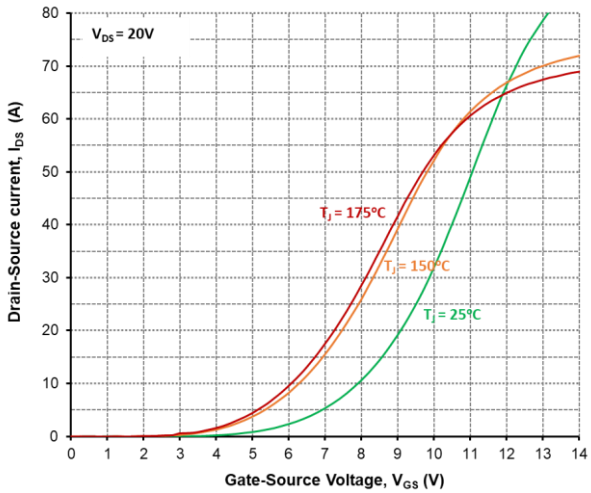


Figure 6. Transfer Characteristic For Various Junction Temperatures

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Typical Performance

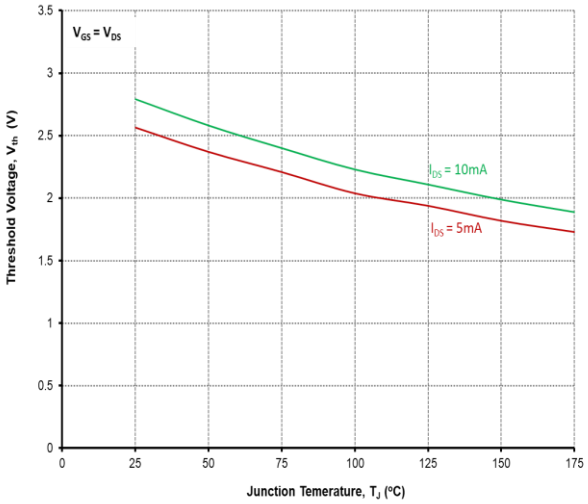


Figure 7. Threshold Voltage vs. Temperature

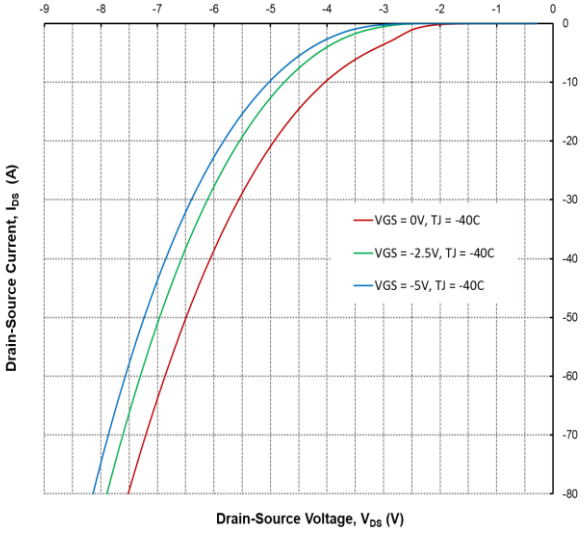


Figure 8. Body Diode Characteristics @ -40°C

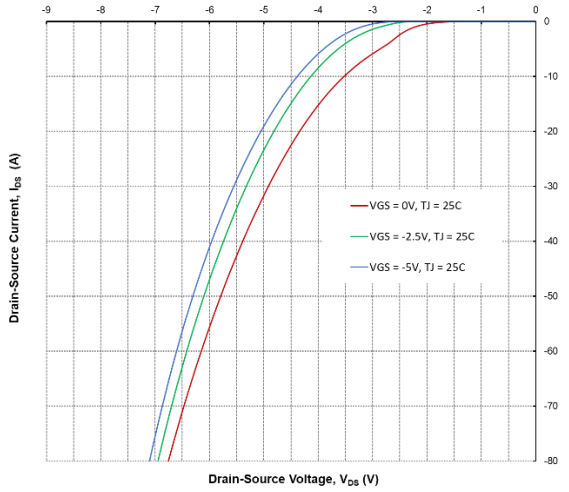


Figure 9. Body Diode Characteristics @ 25°C

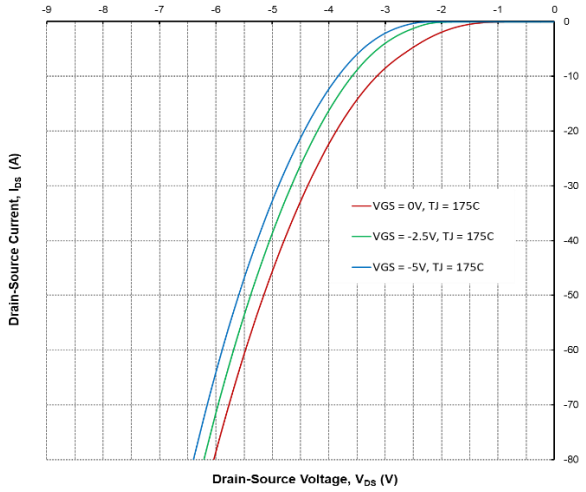


Figure 10. Body Diode Characteristics @ 175°C

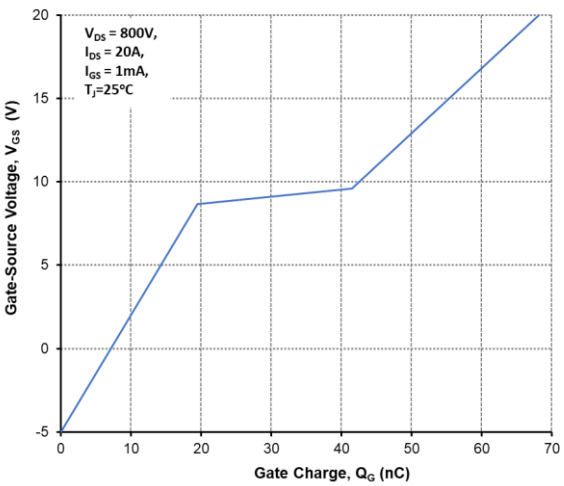


Figure 11. Gate Charge Characteristics

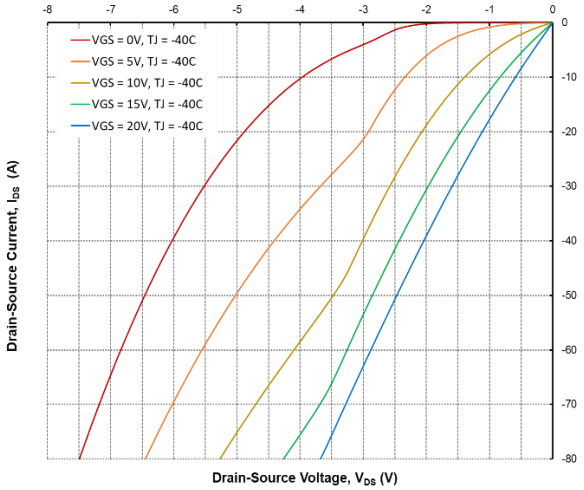


Figure 12. 3rd Quadrant Characteristics @ -40°C

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Typical Performance

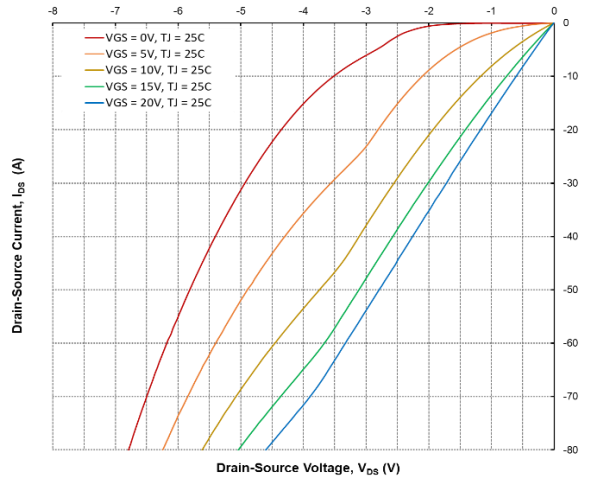


Figure 13. 3rd Quadrant Characteristics @ 25ºC

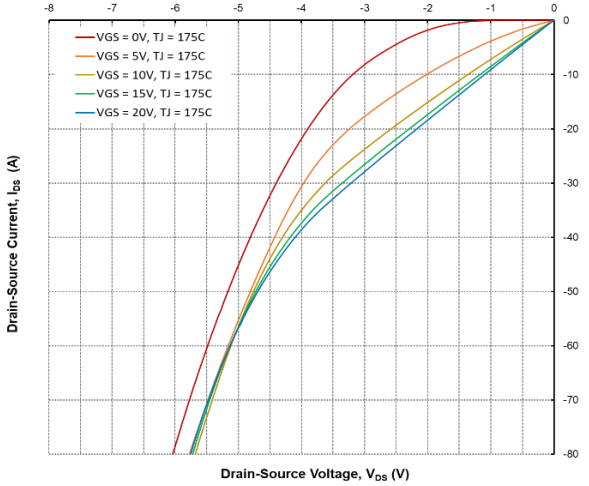


Figure 14. 3rd Quadrant Characteristics @ 175ºC

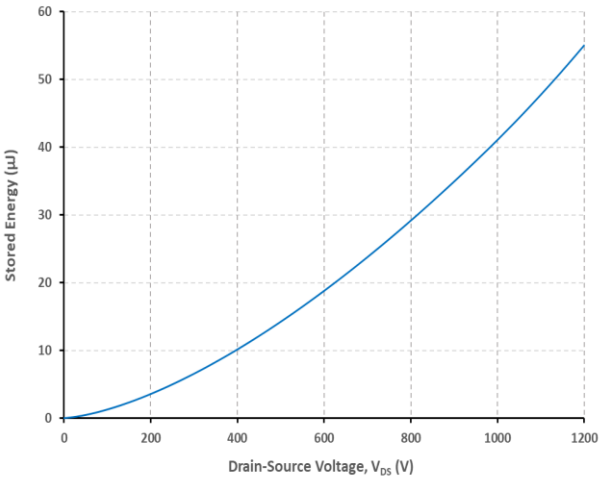


Figure 15. Output Capacitor Stored Energy

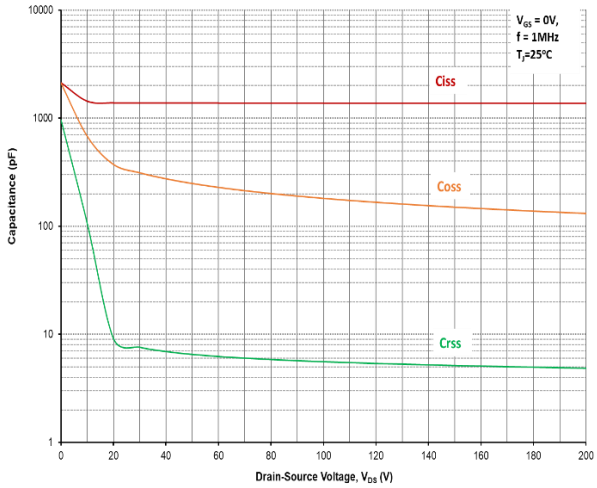


Figure 16. Capacitances vs. Drain-Source Voltage (0-200V)

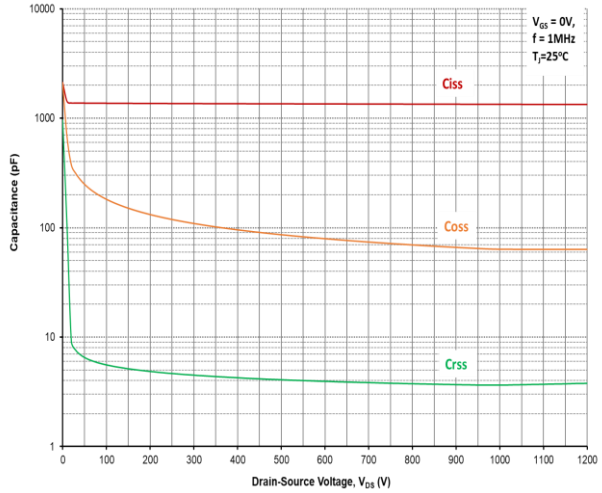


Figure 17. Capacitances vs. Drain-Source Voltage (0-1200V)

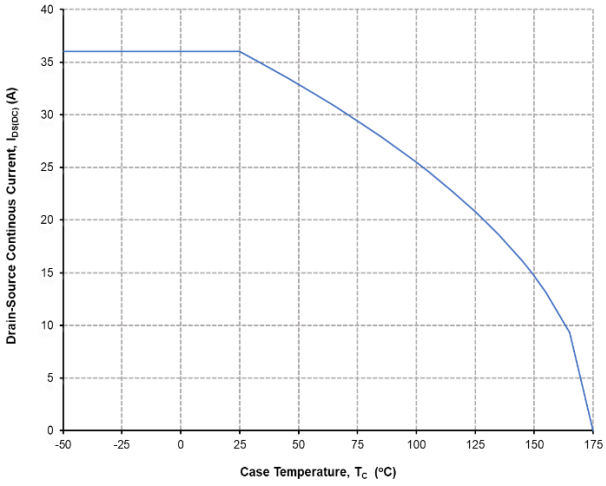


Figure 18. Continuous Drain Current Derating vs. Case Temperature

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Typical Performance

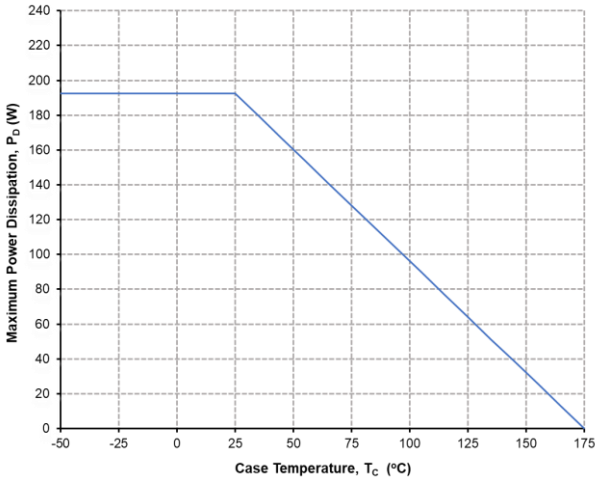


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

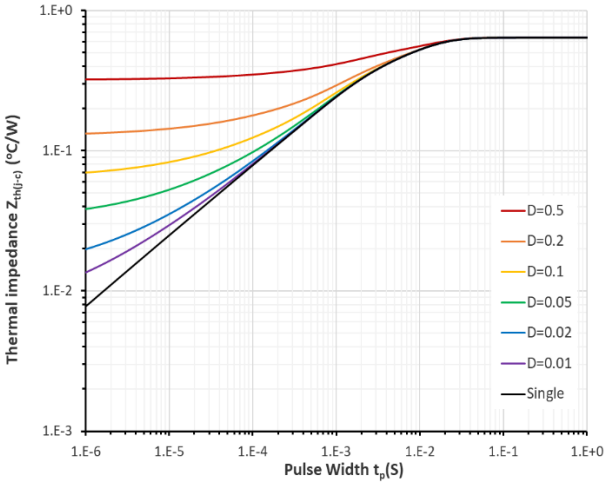


Figure 20. Transient Thermal Impedance (Junction to Case)

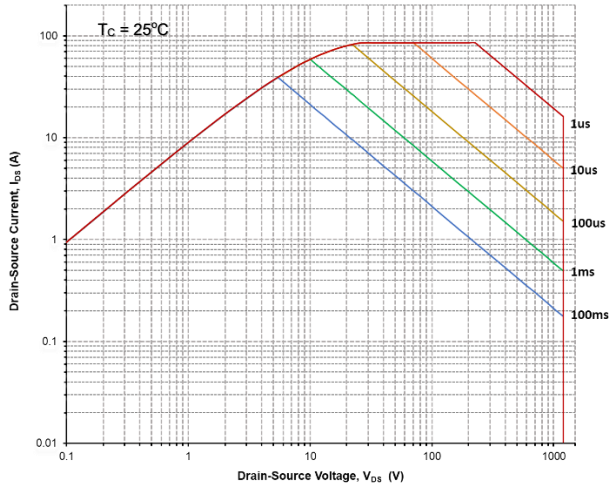


Figure 21. Safe Operating Area

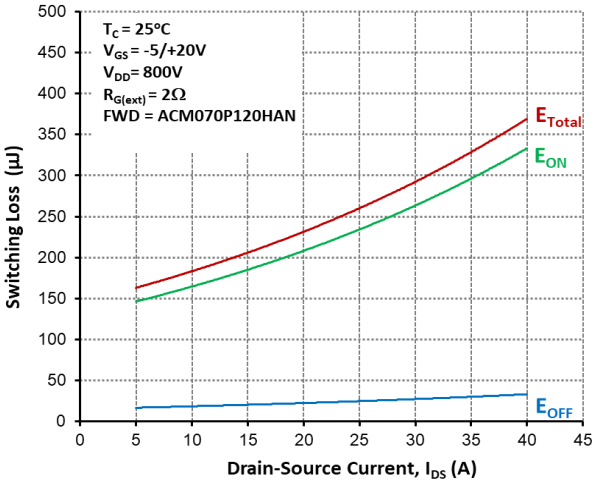


Figure 22. Switching energy vs Drain current

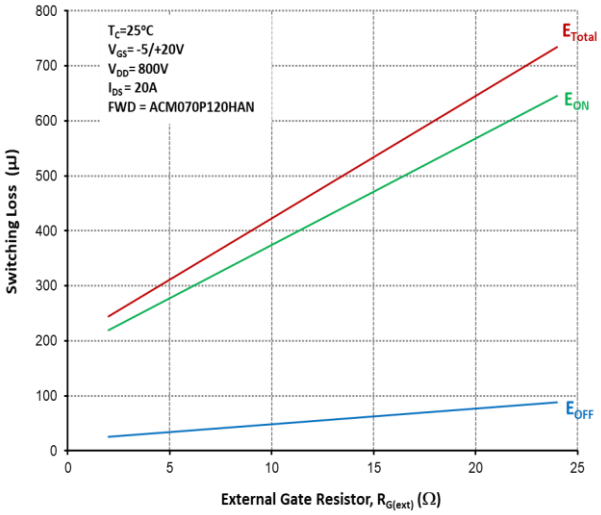


Figure 17. Switching energy vs External Gate Resistor

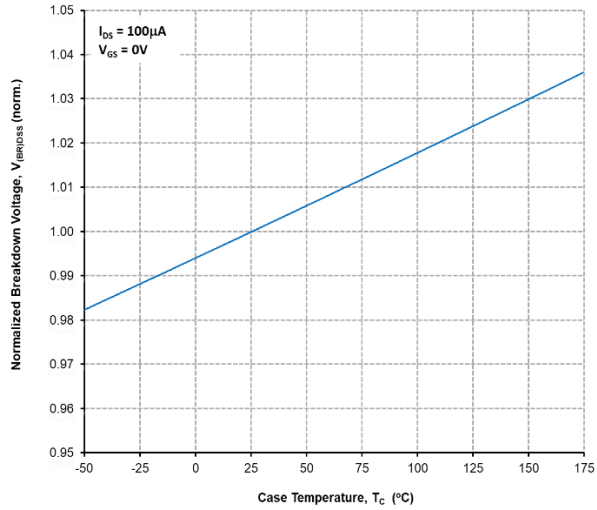
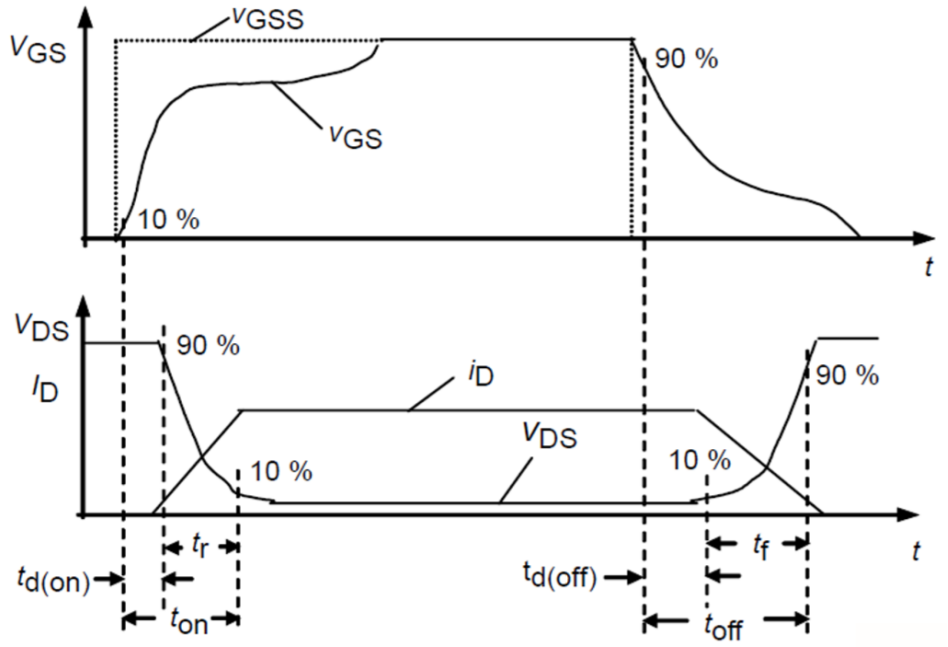
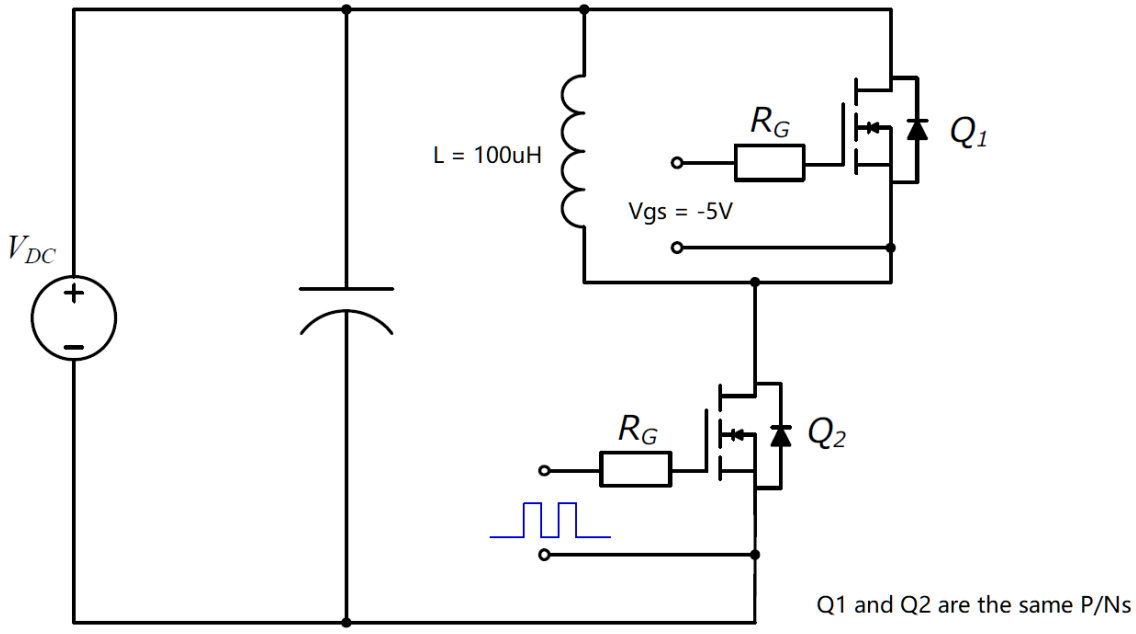


Figure 18. Normalized breakdown voltage vs Temperature

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Switching Times Definition and Test Circuit





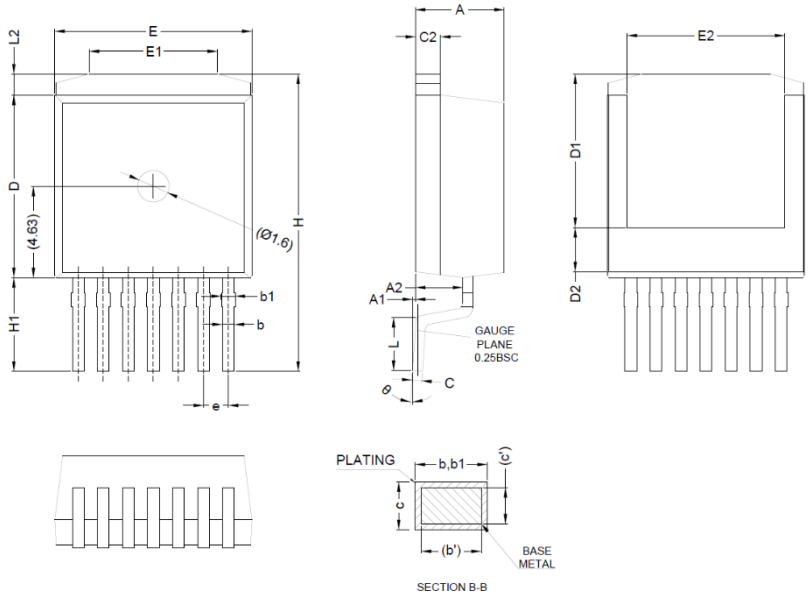
Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

LGE3M70120J

Silicon Carbide Power MOSFET

Package Dimensions

(TO-263-7 Package)



Items	Min	Max
A	4.30	4.70
A1	-	0.25
A2	2.20	2.60
b	0.52	0.72
b'	0.50	0.70
b1	0.60	0.80
c	0.42	0.62
c'	0.40	0.60
c2	1.07	1.47
D	9.05	9.45
D1	7.58	7.98
D2	2.05	2.45
e	1.27 BSC	
E	9.80	10.20
E1	6.30	6.70
E2	7.80	8.20
L	2.48	2.88
L2	0.87	1.27
H	14.87	15.27
H1	4.55	4.95
θ	0°	8°

NOTE ;
1. DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
3. RADIUS ON TERMINAL IS OPTIONAL.
4. GENERAL TOLERANCES - LINEAR ±0.05
5. PLASTIC BODY RADIUS: MAX. 0.25 UNLESS OTHERWISE SPECIFIED.
6. PLASTIC BODY FINISHING: MATT FINISHING Ra=1.8~2.2 MICRONS
7. MISMATCH MAX.=0.05 (CAVITY TO HOLE AXIS)}
8. DIMENSION DO NOT INCLUDE BURR OR MOLD FLASH.

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.